

P-Channel 200 V (D-S) MOSFET

DESCRIPTION

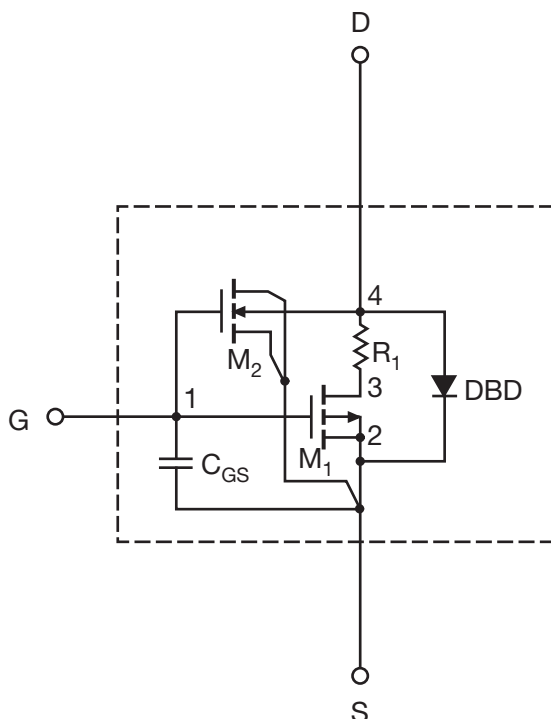
The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



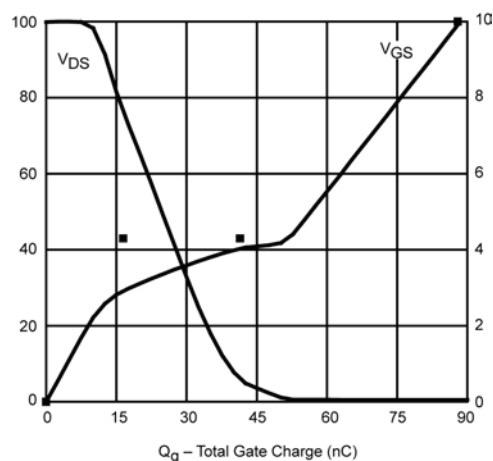
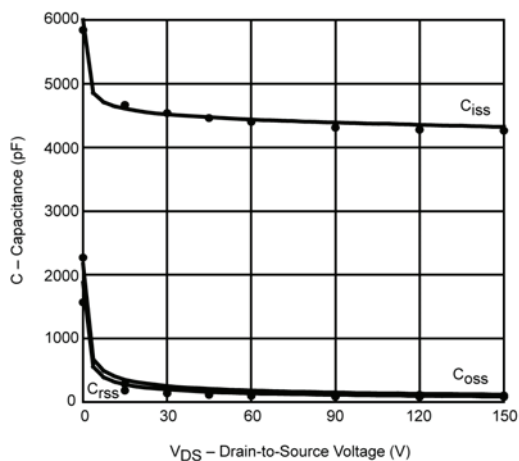
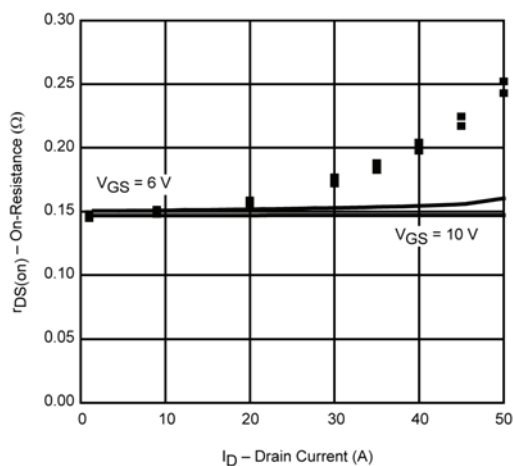
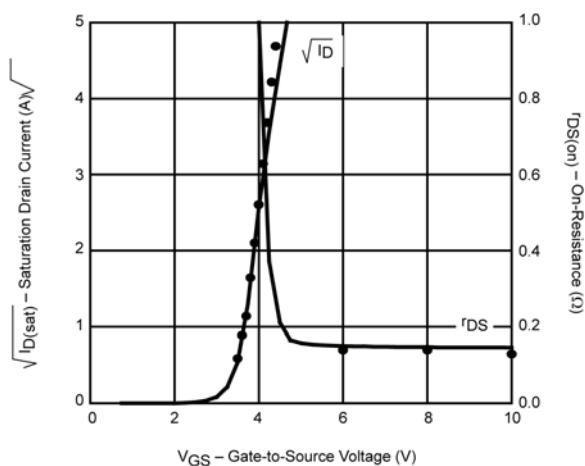
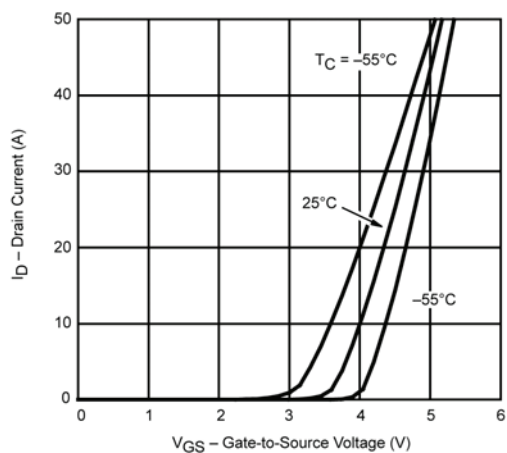
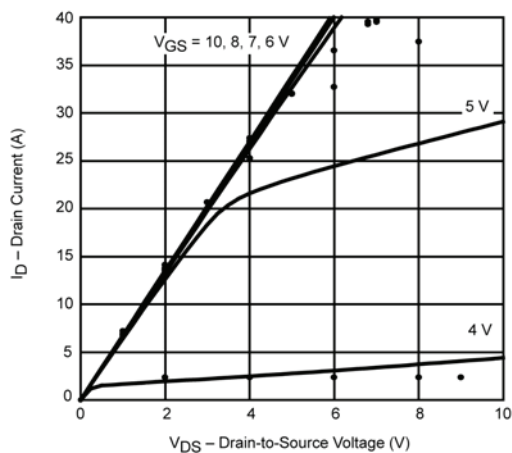
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\ \mu\text{A}$	2.8	-	V
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -10\ \text{V}$, $V_{GS} = -10\ \text{V}$	34	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\ \text{V}$, $I_D = -3.8\ \text{A}$	0.150	0.145	Ω
		$V_{GS} = -6\ \text{V}$, $I_D = -3.6\ \text{A}$	0.147	0.147	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\ \text{V}$, $I_D = -3.8\ \text{A}$	18	17	S
Diode Forward Voltage	V_{SD}	$I_S = -4.2\ \text{A}$, $V_{GS} = 0\ \text{V}$	-0.84	-0.78	V
Dynamic^b					
Total Gate Charge	Q_g	$V_{DS} = -100\ \text{V}$, $V_{GS} = -10\ \text{V}$, $I_D = -3.8\ \text{A}$	89	88	nC
Gate-Source Charge	Q_{gs}		16.5	16.5	
Gate-Drain Charge	Q_{gd}		25	25	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\ \%$.
b. Guaranteed by design, not subject to production testing.



COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25^\circ\text{C}$, unless otherwise noted)



Note

- Dots and squares represent measured data.